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Amendments to the Claims:

A clean version of the entire set of pending claims (including amendments to the claims, if any) is submitted herewith per 37 CFR 1.121(c). This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

- 1.-14. (Cancelled).
- 15. (Currently Amended) An apparatus as recited in claim [[14]]20, wherein said upper electrode comprises: a cooling plate having a plurality of gas supply holes, which supply the gas; a gas introducing plate having gas holes, which introduce the gas into a semiconductor wafer; and further comprises a jig, which fixes said gas-introducing plate to said cooling plate.
- 16. (Currently Amended) An apparatus as recited in claim [[14]]20, wherein said first plasma detecting device is provided between said gas-introducing plate and said cooling plate.
- 17. (Currently Amended) An apparatus as recited in claim [[14]] 20, wherein said first pressure increases as said gas holes of said gas-introducing plate increase in size.
- 18. (Currently Amended) An apparatus as recited in claim 15, wherein said first pressure gaugeplasma detecting device is at a backside of said gas introducing plate.

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- 19. (Cancelled).
- 20. (New). An apparatus for etching a wafer, comprising: an upper gas electrode, which has a cooling plate provided with gas supply holes and a gas-introducing plate with a plurality of gas holes;
 - a lower gas electrode over which the wafer is placed;
- a first pressure gauge, which detects a first pressure between the cooling plate and the gas-introducing plate;
- a second pressure gauge, which detects a second pressure between the gas-introducing plate and the lower electrode;
- a detector, which detects a difference between the first pressure and the second pressure, and which terminates the etching of the wafer when the difference in the pressure is greater than a predetermined value.

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